2SD1633

Silicon NPN triple diffusion planar type darlington

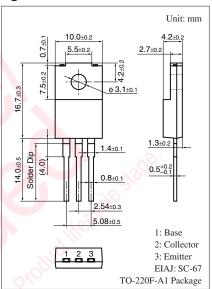
For voltage switching

■ Features

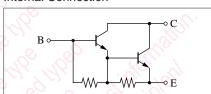
- High-speed switching
- Satisfactory linearity of forward current transfer ratio h_{FE}
- Full-pack package which can be installed to the heat sink with one screw

■ Absolute Maximum Ratings $T_C = 25$ °C

Parameter	Symbol	Rating	Unit	
Collector-base voltage (Emitter open)	V _{CBO}	100	V	
Collector-emitter voltage (Base open)	V_{CEO}	100	V	
Emitter-base voltage (Collector open)	V_{EBO}	7	V	
Collector current	I_{C}	5	A	
Peak collector current	I_{CP}	8	A	
Base current	I_{B}	0.5	A	
Collector power dissipation	P _C	30	W	
$T_a = 25^{\circ}C$		2.0		
Junction temperature	T_{j}	150	°CO	
Storage temperature	T_{stg}	-55 to +150	°C	
			9 . 0	



Internal Connection



■ Electrical Characteristics $T_C = 25^{\circ}C \pm 3^{\circ}C$

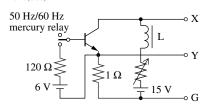
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-emitter sustaining voltage *2	V _{CEO(SUS)}	$I_C = 0.2 \text{ A}, L = 25 \text{ mH}$	100	0///		V
Collector-base cutoff current (Emitter open)	I_{CBO}	$V_{CB} = 100 \text{ V}, I_E = 0$	D. 10	0.7	100	μΑ
Collector-emitter cut-off current (Base open)	I_{CEO}	$V_{CE} = 100 \text{ V}, I_B = 0$	~ 6 ₀ .		100	μΑ
Emitter-base cutoff current (Collector open)	I_{EBO}	$V_{EB} = 7 \text{ V}, I_C = 0$			5	mA
Forward current transfer ratio *1	h _{FE}	$V_{CE} = 3 \text{ V}, I_{C} = 3 \text{ A}$	1500		15 000	_
Collector-emitter saturation voltage	V _{CE(sat)}	$I_C = 3 \text{ A}, I_B = 3 \text{ mA}$			1.5	V
Base-emitter saturation voltage	V _{BE(sat)}	$I_C = 3 \text{ A}, I_B = 3 \text{ mA}$			2.0	V
Transition frequency	f_T	$V_{CE} = 10 \text{ V}, I_{C} = 1 \text{ A}, f = 1 \text{ MHz}$		15		MHz
Turn-on time	t _{on}	$I_C = 3 \text{ A}, I_{B1} = 3 \text{ mA}, I_{B2} = -3 \text{ mA}$			3	μs
Storage time	t _{stg}	$V_{CC} = 50 \text{ V}$			5	μs
Fall time	t _f	, and the second			3	μs

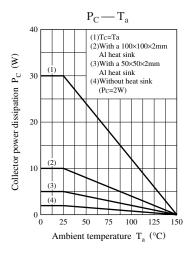
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

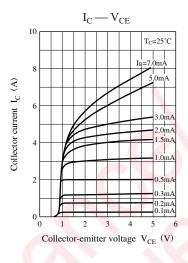
2. *1: Rank classification

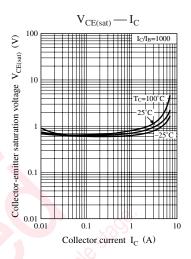
Rank	Q	Р
h_{FE}	1500 to 6000	5 000 to 15 000

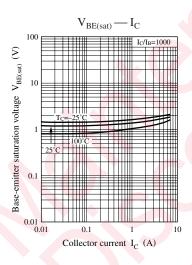
*2: V_{CEO(SUS)} test circuit

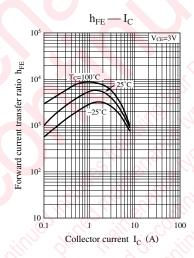


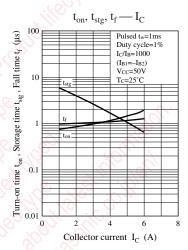


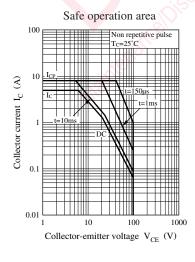


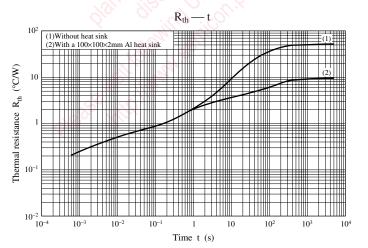












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